

AMENDMENTS TO THE CLAIMS

1. (currently amended) A semiconductor device, comprising:
 - a semiconductor substrate including main and back surfaces and a trimming opening penetrating ~~therethrough~~ through the semiconductor substrate from the back surface to the main surface;
 - an insulating film formed on the main surface of the semiconductor substrate;
 - and
 - a fuse element disposed opposite ~~formed on~~ the main surface of the semiconductor substrate ~~through~~ on the insulating film at a position facing aligned with and electrically isolated from the trimming opening.
2. (currently amended) The semiconductor device as defined in Claim 1, wherein the insulating film remains intact between the fuse element and the trimming opening until a process of cutting the fuse element is performed whereby the insulating film is penetrated.
3. (currently amended) The semiconductor device as defined in Claim 1, further comprising an non-conductive material filled into wherein the trimming opening such that the trimming opening is sealed to prevent contamination of the fuse element from the back surface of the semiconductor substrate.

4. (original) The semiconductor device as defined in Claim 1, wherein the semiconductor device has a contour with a plurality of corner edges which are rounded.

5. (original) The semiconductor device as defined in Claim 4, wherein one of the plurality of corner edges has a curvature greater than those of others of the plurality of corner edges.

6. (currently amended) The semiconductor device as defined in Claim [[1]] 4, wherein the contour of the semiconductor device has a side surface on which predetermined pits and dents representing a bar code are formed.

7. (original) The semiconductor device as defined in Claim 1, wherein the back surface of the semiconductor substrate comprises at least one recess-shaped marking formed thereon.

8. (original) The semiconductor device as defined in Claim 1, wherein the back surface of the semiconductor substrate comprises a marking formed thereon by laser irradiation.

9. (new) A semiconductor device, comprising:

a semiconductor substrate having first and second surfaces, the semiconductor substrate defining at least one opening penetrating through the semiconductor substrate and the first and second surfaces;

a film of insulating material disposed on the second surface of the semiconductor substrate; and

a fuse element corresponding to each opening disposed on the film of insulating material at a side opposite to and isolated from the semiconductor substrate, a trimmable portion of the fuse aligned with the respective opening.

10. (new) The semiconductor device as defined in Claim 9, wherein the insulating film remains intact between the fuse element and the trimming opening until a process of cutting the fuse element is performed whereby the insulating film is penetrated.

11. (new) The semiconductor device as defined in Claim 9, further comprising a non-conductive material filled into the trimming opening such that the trimming opening is sealed from the back surface of the semiconductor substrate to prevent contamination of the fuse element.

12. (new) The semiconductor device as defined in Claim 9, wherein the semiconductor device has a contour with a plurality of corner edges which are rounded.

13. (new) The semiconductor device as defined in Claim 12, wherein one of the plurality of corner edges has a curvature greater than those of others of the plurality of corner edges.

14. (new) The semiconductor device as defined in Claim 12, wherein the contour of the semiconductor device has a side surface on which predetermined pits and dents representing a bar code are formed.

15. (new) The semiconductor device as defined in Claim 9, wherein the back surface of the semiconductor substrate comprises at least one recess-shaped marking formed thereon.

16. (new) The semiconductor device as defined in Claim 9, wherein the back surface of the semiconductor substrate comprises a marking formed thereon by laser irradiation.